

WCM-Forum

Surface potential vs. charge-based MOSFET models

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Outline:

- I-V characteristic
- Total charges

Pao-Sah current expression

$$I_{DS} = \frac{\mu W}{L} \int_{V_S}^{V_D} (-Q'_I) dV_C$$

Charge Control Model

$$V_P - V_C = \frac{Q'_{IP} - Q'_I}{nC'_{ox}} + \phi_t \ln\left(\frac{Q'_I}{Q'_{IP}}\right)$$

S.I.

$$-Q'_I \approx nC'_{ox}(V_P - V_C)$$

W.I

$$Q'_I \approx Q'_{IP} e^{-\frac{V_P - V_C}{\phi_t}}$$

Q'_{IP} : pinch-off charge ϕ_t : thermal voltage

V_P : pinch-off voltage n : slope factor

I-V Compact Models

$$I_{DS} = -\mu \frac{W}{L} \int_{Q'_{IS}}^{Q'_{ID}} Q'_I \frac{dV_C}{dQ'_I} dQ'_I$$

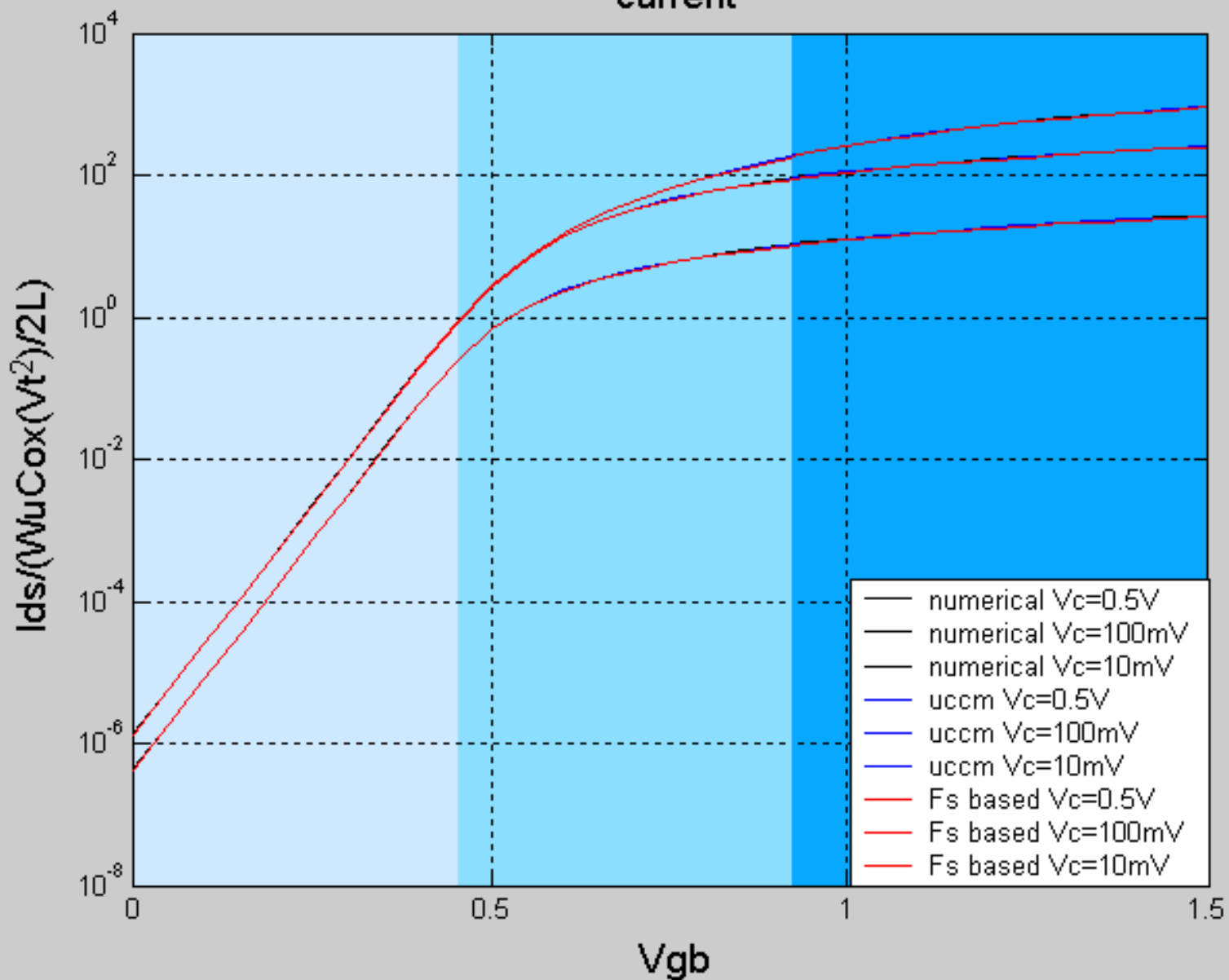
Charge-based model

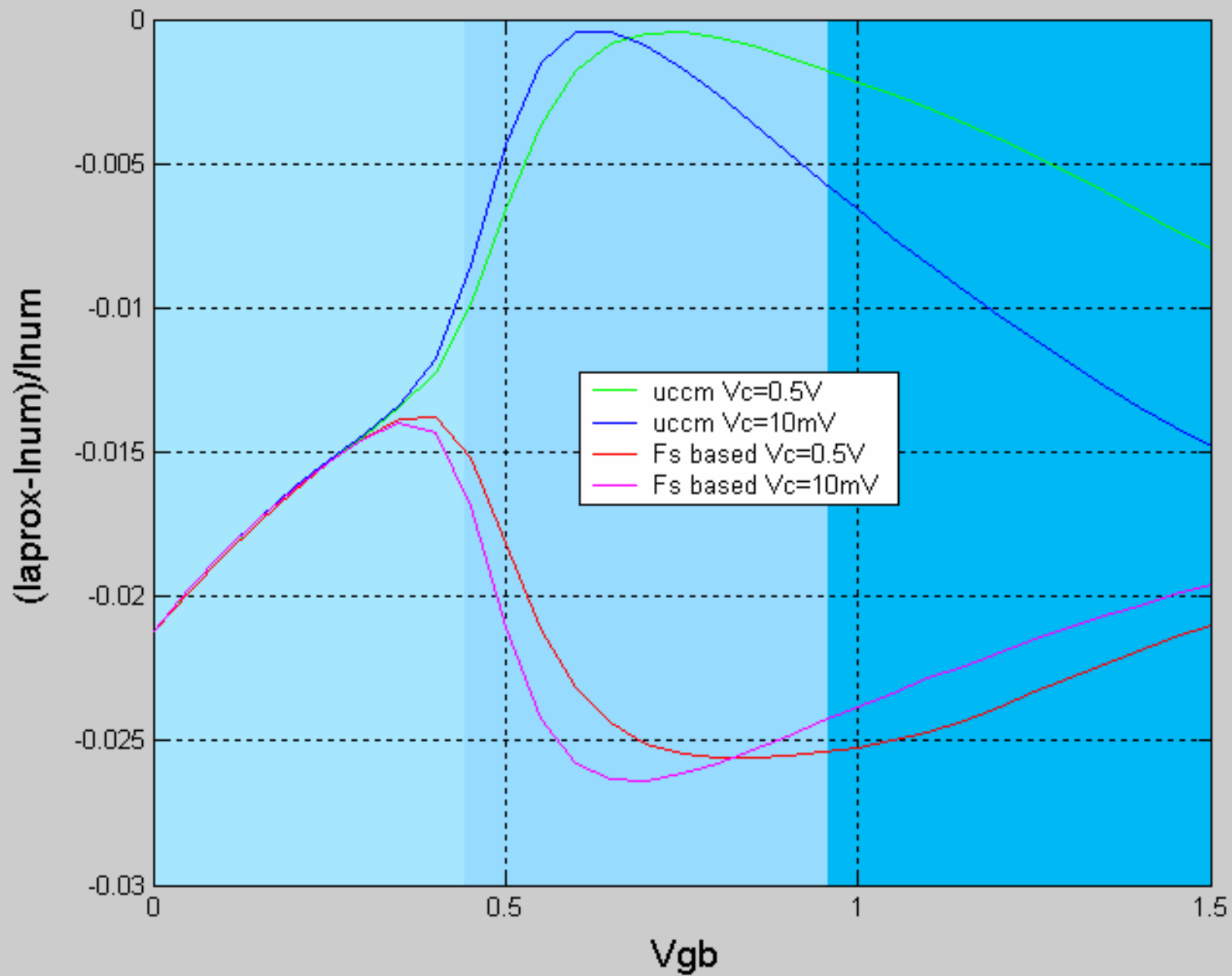
$$I_{DS} = \frac{\mu W}{L} \int_{V_S}^{V_D} (-Q'_I) dV_C$$

$$I_{DS} = -\mu \frac{W}{L} \int_{\phi_{s0}}^{\phi_{sL}} Q'_I(\phi_s) \frac{dV_C}{d\phi_s} d\phi_s$$

Surface potential model

current





Total charges

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Table 1. Auxiliary functions and parameters

Quantity	Expression
Q'_F	$Q'_I(V_{SB}, V_{GB}) - nC'_{ox}\phi_1$
Q'_R	$Q'_I(V_{DB}, V_{GB}) - nC'_{ox}\phi_1$

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Table 2. Drain current, total charges and small signal parameters

Quantity	Expression
Q_I	$WL \left[\frac{2Q_F'^2 + Q_F'Q_R' + Q_R'^2}{3(Q_F' + Q_R')} + nC'_{ox}\phi_1 \right]$
Q_S	$WL \left[\frac{6Q_F'^3 + 12Q_R'Q_F'^2 + 8Q_R'^2Q_F' + 4Q_R'^3}{15(Q_F' + Q_R')^2} + \frac{n}{2}C'_{ox}\phi_1 \right]$

MOSFET compact models

